MBR20200CT

MAXIMUM RATINGS (Per Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	200	V
Average Rectified Forward Current (T _C = 161°C) Per Leg Per Package	I _{F(AV)}	10 20	А
Peak Repetitive Forward Current per Leg (Square Wave, 20 kHz, T _C = 158°C)	I _{FRM}	20	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I _{FSM}	150	А
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I _{RRM}	1.0	Α
Storage Temperature Range	T _{stg}	-65 to +175	°C
Operating Junction Temperature	TJ	-65 to +175	°C
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Condition	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case	Minimum Pad	$R_{\theta JC}$	2.0	°C/W
Maximum Thermal Resistance, Junction-to-Ambient	Minimum Pad	$R_{\theta JA}$	60.0	°C/W

ELECTRICAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Min	Typical	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1)	V _F	1111	0.80 0.66 0.89 0.76	0.90 0.80 1.00 0.90	V
Maximum Instantaneous Reverse Current (Note 1) (Rated dc Voltage, T _J = 25°C) (Rated dc Voltage, T _J = 125°C)		- 1	0.0002 0.4	1.0 50	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

DYNAMIC CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit
Capacitance ($V_R = -5.0 \text{ V}$, $T_C = 25^{\circ}\text{C}$, Frequency = 1.0 MHz)	C _T	500	pF

^{1.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

MBR20200CT

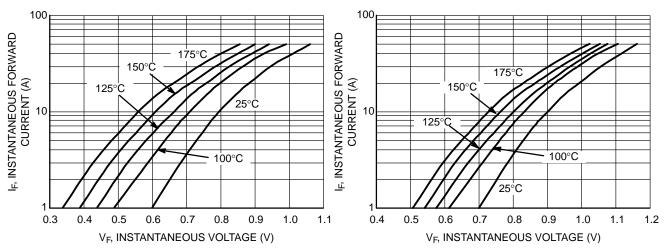


Figure 1. Typical Forward Voltage

Figure 2. Maximum Forward Voltage

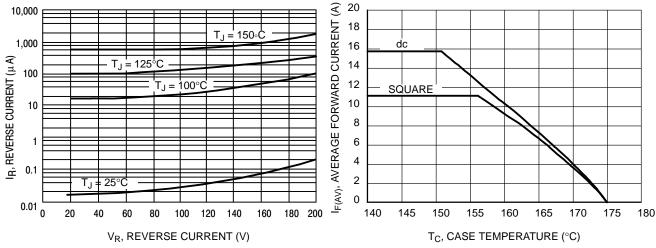


Figure 3. Typical Reverse Current (Per Leg)

Figure 4. Current Derating, Case, Per Leg

MBR20200CT

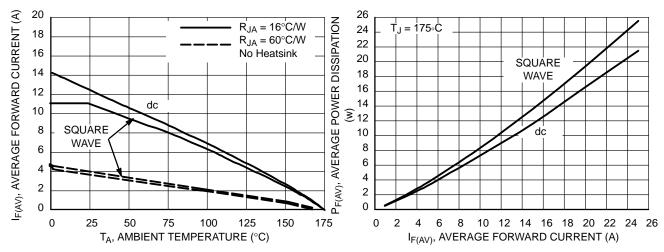


Figure 5. Current Derating, Ambient, Per Leg

Figure 6. Forward Power Dissipation

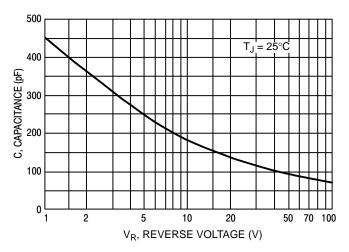


Figure 7. Typical Capacitance (Per Leg)

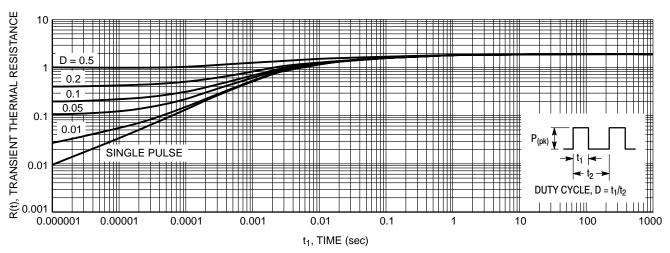
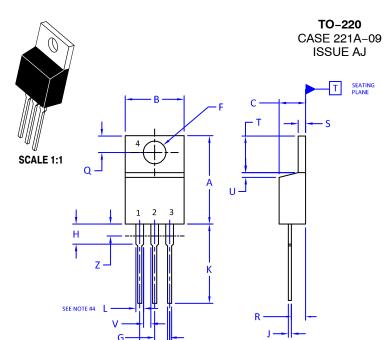


Figure 8. Thermal Response Junction-to-Case





DATE 05 NOV 2019

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMETERS	
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

	STYLE 2:		STYLE 3:		STYLE 4:	
BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
	STYLE 6:		STYLE 7:		STYLE 8:	
GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELA
DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
	STYLE 10:		STYLE 11:		STYLE 12	:
GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
EMITTER	3.	DRAIN	3.	GATE	3.	GATE
COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED
	COLLECTOR EMITTER COLLECTOR GATE DRAIN SOURCE DRAIN GATE COLLECTOR EMITTER	BASE PIN 1. COLLECTOR 2. EMITTER 3. COLLECTOR 4. STYLE 6: PIN 1. GATE PIN 1. DRAIN 2. SOURCE 3. DRAIN 4. STYLE 10: GATE PIN 1. COLLECTOR 2. EMITTER 3.	BASE	BASE COLLECTOR PIN 1. 2. EMITTER BASE 2. EMITTER PIN 1. 2. EMITTER GOLLECTOR 3. COLLECTOR 3. 4. EMITTER 4. GATE DRAIN STYLE 7: PIN 1. ANODE PIN 1. PIN 1. PI	BASE	BASE

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